

1. General description

Planar passivated high commutation three quadrant triac in a TO220 plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The sensitive gate "series E" is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

4. Quick reference data

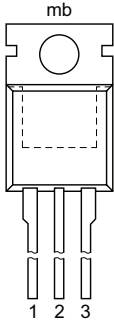
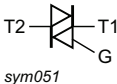
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Absolute maximum rating						
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 101\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	16	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	140	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	150	A
T_j	junction temperature		-	-	125	°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 7	-	-	10	mA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _H	holding current	V _D = 12 V; T _j = 25 °C; Fig. 9		-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; Fig. 10		-	1.3	1.5	V
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		60	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit		5	-	-	A/ms
		V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 10 V/μs; gate open circuit		8	-	-	A/ms
		V _D = 400 V; T _j = 125 °C; I _{T(RMS)} = 16 A; dV _{com} /dt = 1 V/μs; gate open circuit		12	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA316-600E	TO220	BTA316-600E,127	Tube	50	SOT78	13-Jun-2008
BTA316-600E/DG		BTA316-600E/DGQ	Tube	50	SOT78 (Halogen free)	13-Jun-2008

7. Marking

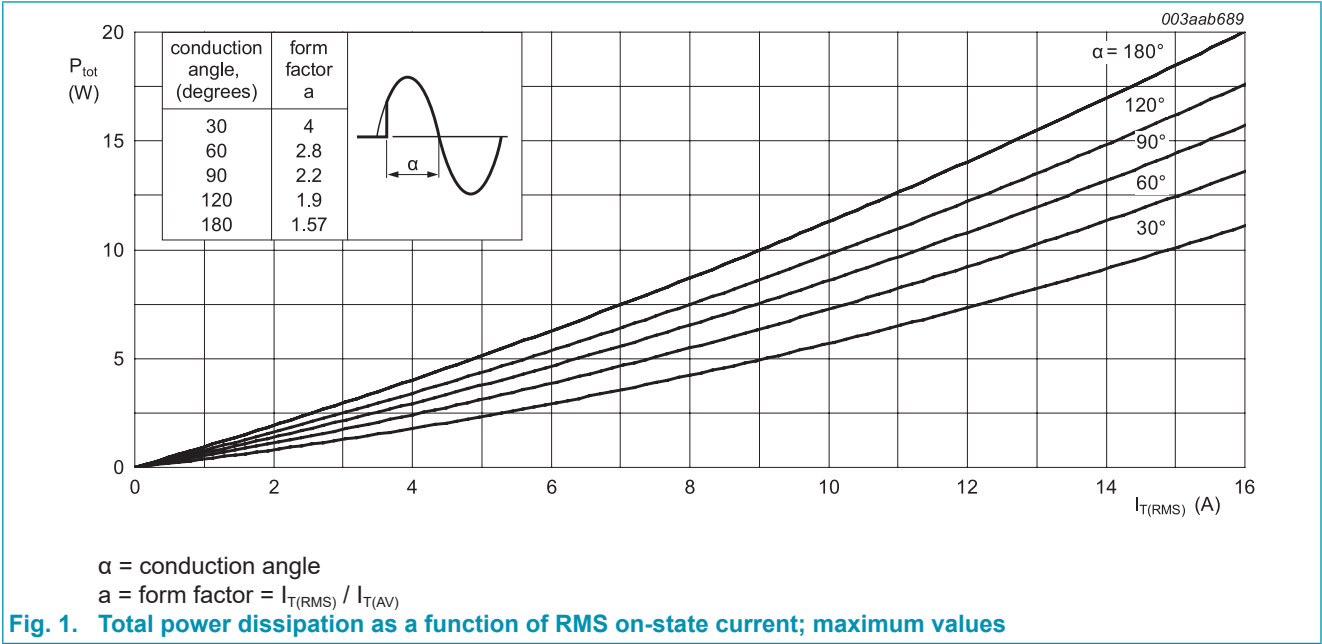
Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: d	Assembly factory: A
BTA316-600E	BTA316 600E PJdxxxx xx	BTA316 600E PJAxxxx xx
BTA316-600E/DG	BTA316 600EDG PJdxxxx xx	BTA316 600EDG PJAxxxx xx

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 101\text{ }^{\circ}\text{C}$; Fig 1; Fig 2; Fig 3		-	16	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig 4; Fig 5		-	140	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		-	150	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse		-	98	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{G}} = 0.2\text{ A}$		-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	2	A
P_{GM}	peak gate power			-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.5	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature			-	125	$^{\circ}\text{C}$



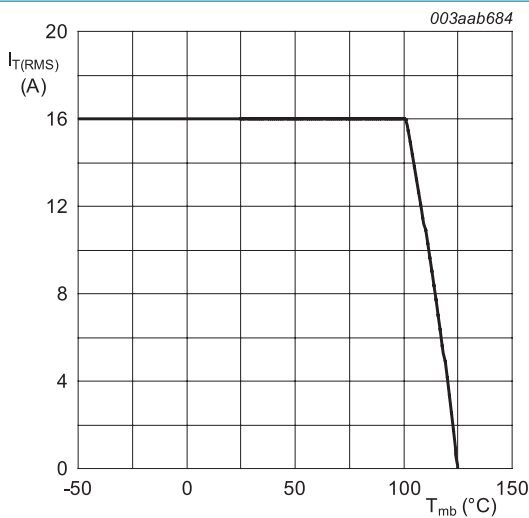
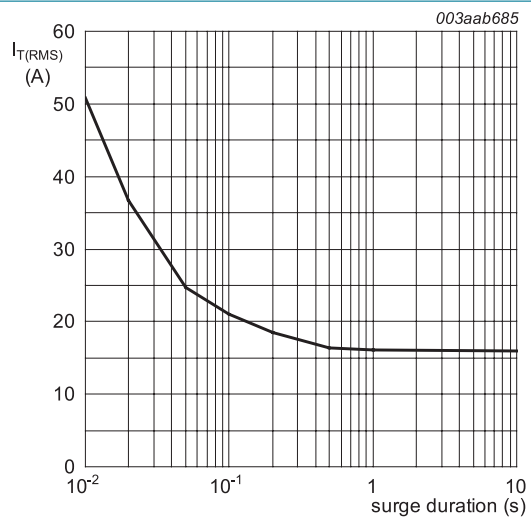
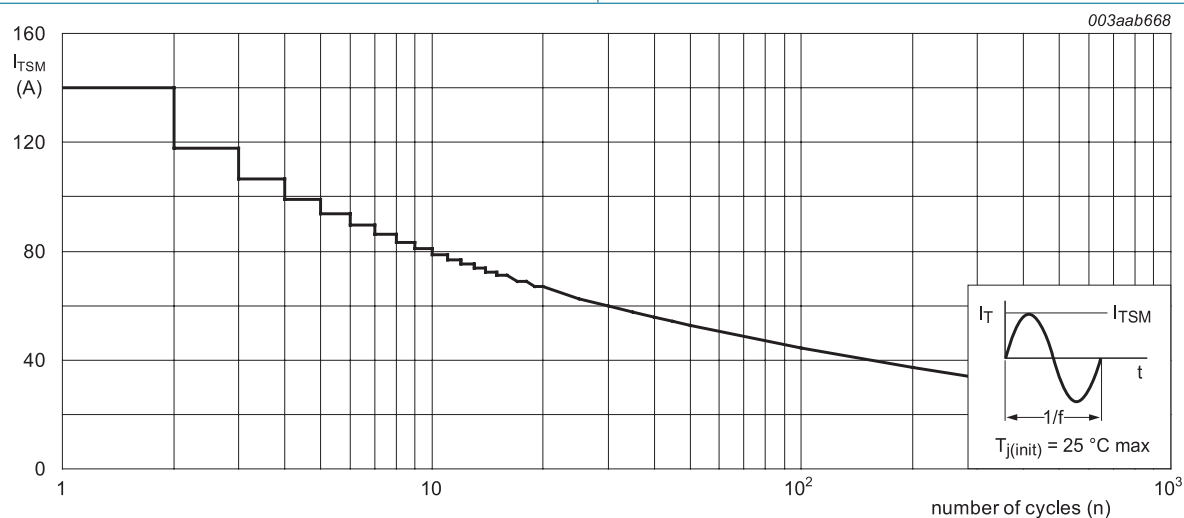


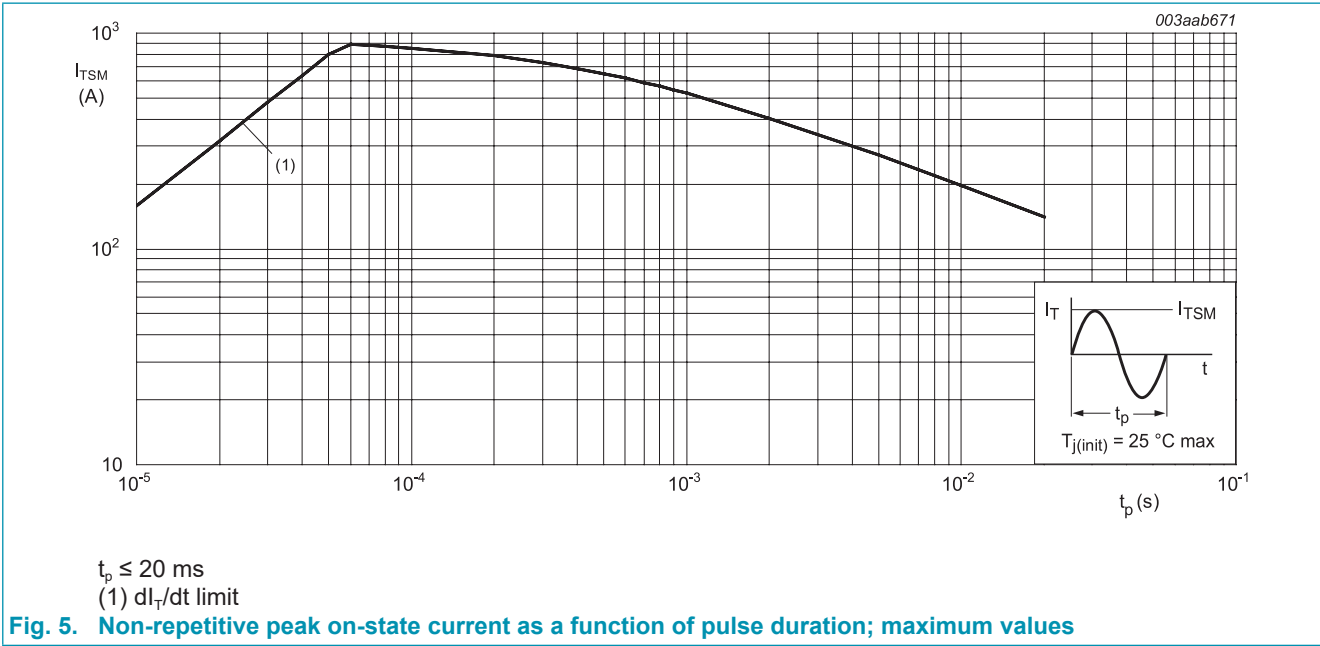
Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; $T_{mb} = 101\text{ °C}$
Fig. 3. RMS on-state current as a function of surge duration; maximum values



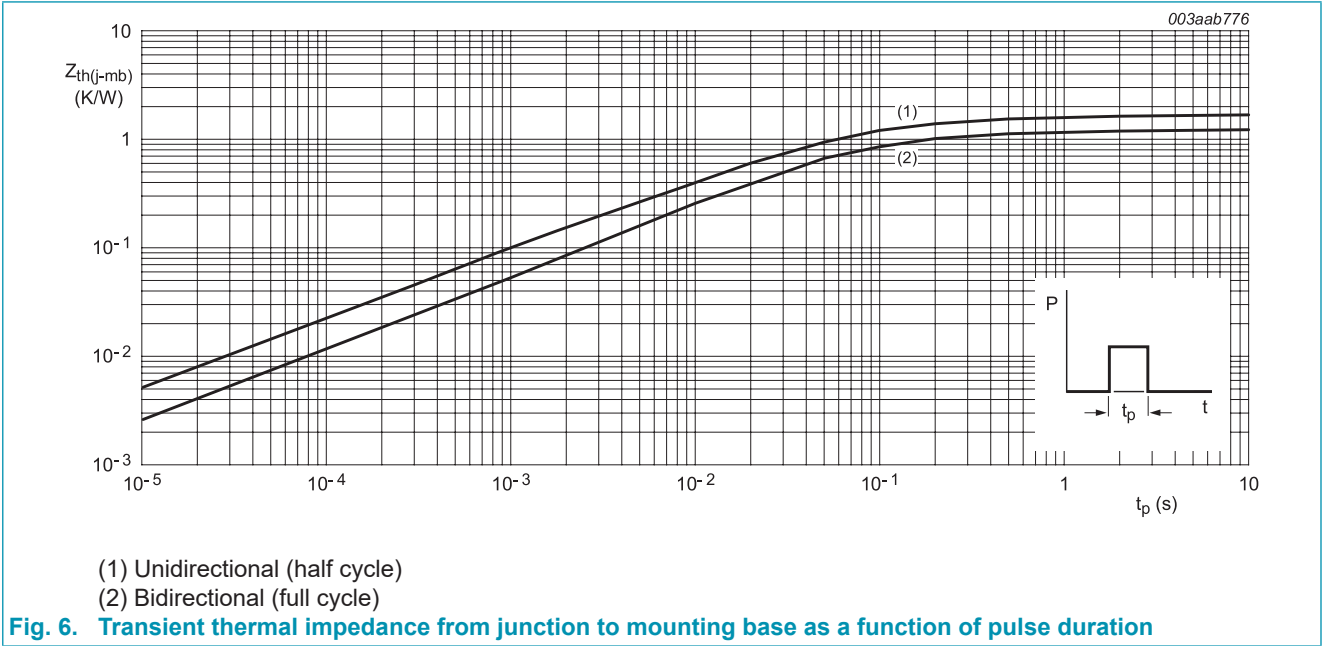
f = 50 Hz
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

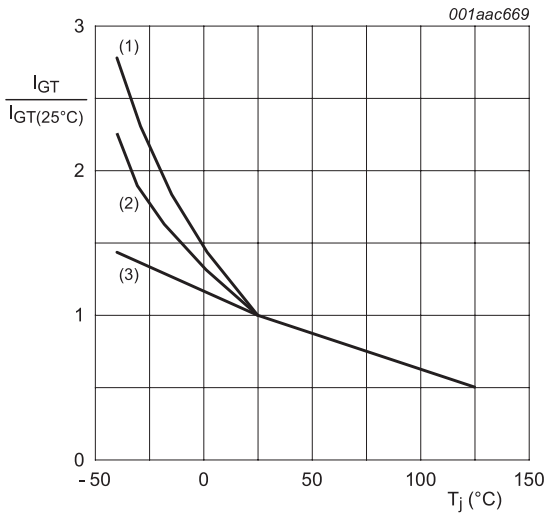
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig 6		-	-	1.2	K/W
		half cycle; Fig 6		-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 7		-	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	-	25	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	-	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_J = 25\text{ }^\circ\text{C}$; Fig. 8		-	-	30	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	15	mA
V_T	on-state voltage	$I_T = 18\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 10		-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 25\text{ }^\circ\text{C}$; Fig. 11		-	0.8	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$		0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit		60	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit		5	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit		8	-	-	A/ms
		$V_D = 400\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 16\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit		12	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

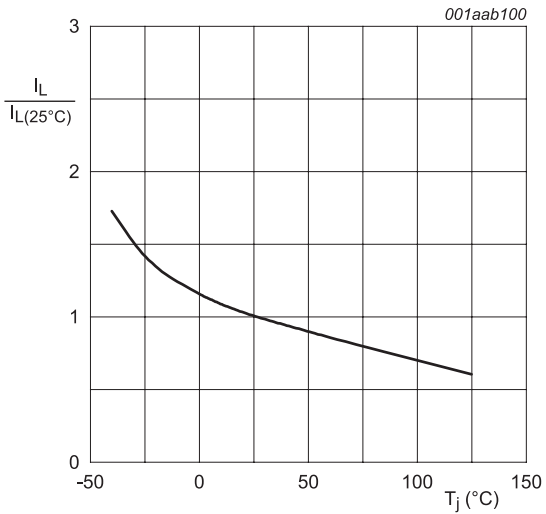


Fig. 8. Normalized latching current as a function of junction temperature

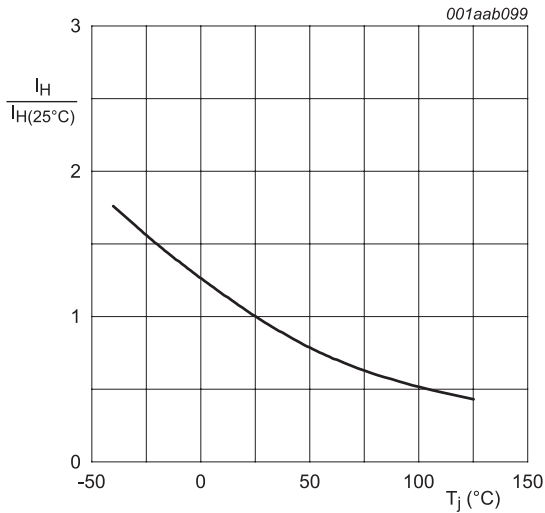
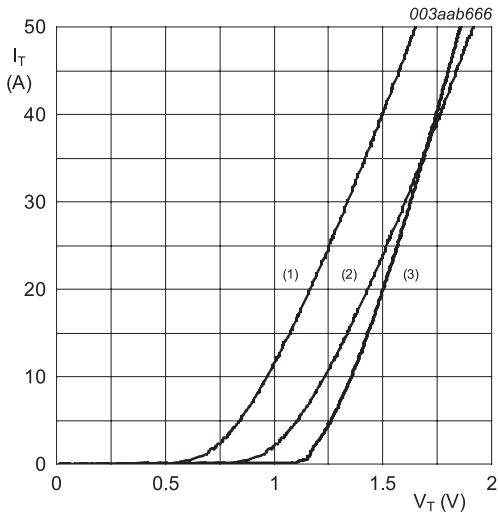


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.024\text{ V}; R_s = 0.021\text{ }\Omega$
- (1) $T_j = 125^{\circ}\text{C}$; typical values
 - (2) $T_j = 125^{\circ}\text{C}$; maximum values
 - (3) $T_j = 25^{\circ}\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

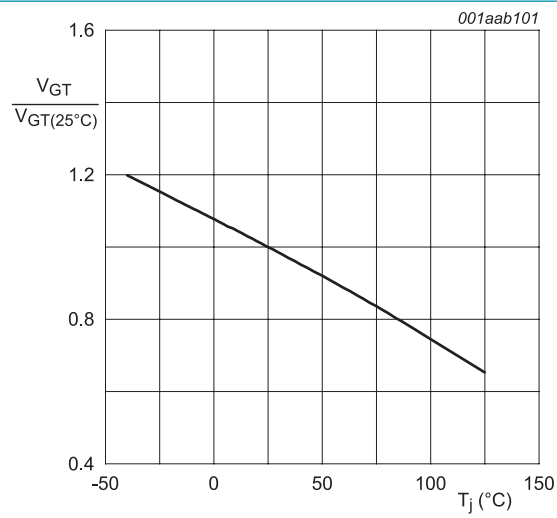


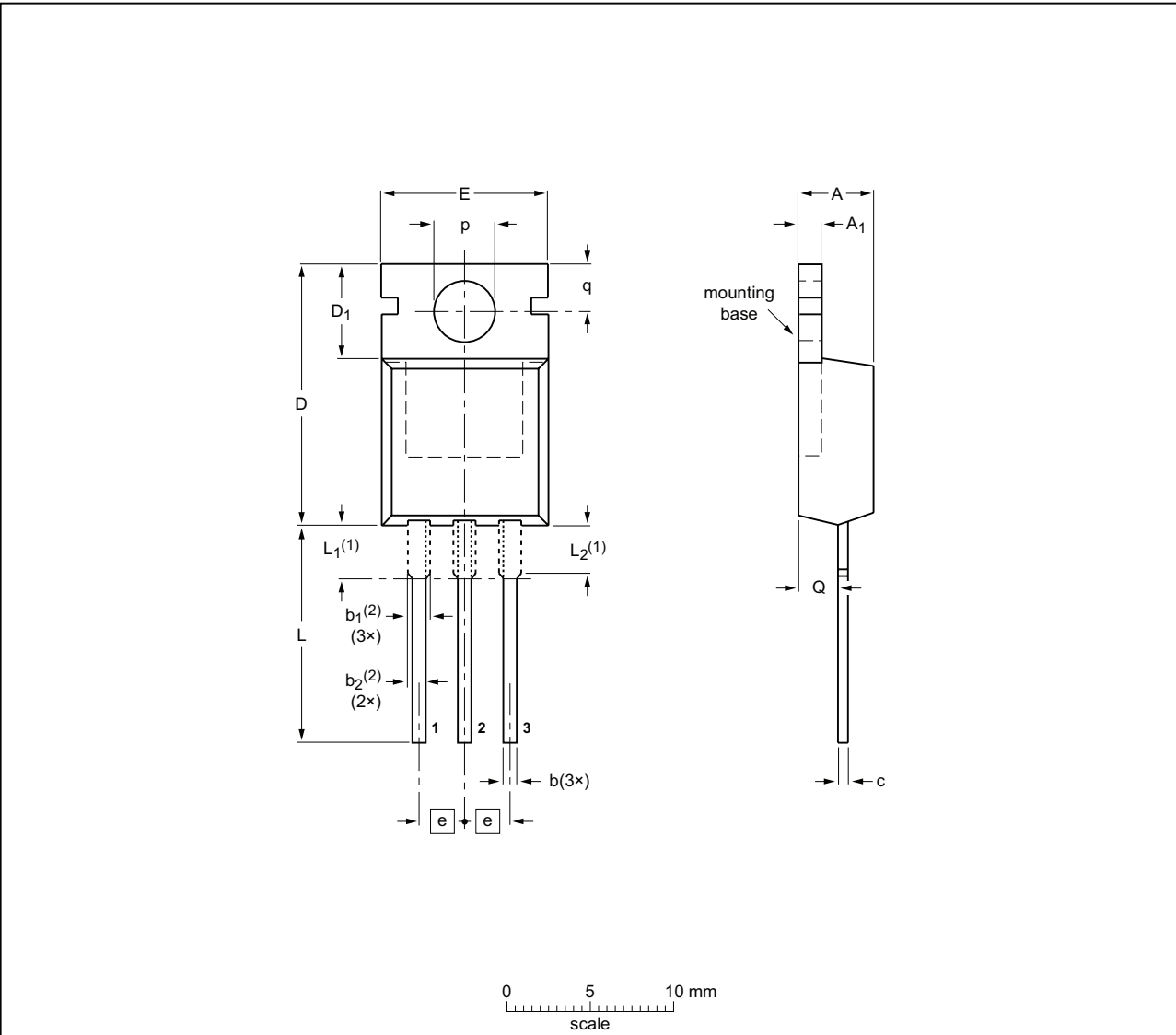
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Assembly factory: d & A

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

- Notes
- 1. Lead shoulder designs may vary.
 - 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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